

Monday Dec. 14		
Room A		
7:00-8:00AM	Breakfast	
Session: Crystal Engineering I Chair: Cristian V. Ciobanu		
8:00-8:25AM	A01: Laser-irradiation-induced crystallization of Si films: scientific opportunities and technological motivations	James Im Columbia University, USA
8:25-8:50AM	A02: Multi crystalline silicon solidification under controlled forced convection	Kader Zaidat Institut Polytechnique de Grenoble – PHELMA, France
8:50-9:15AM	A03: Thermodynamic Phase Behavior of Cocrystal Systems	Gabriele Sadowski TU Dortmund, Germany
9:15-9:40AM	A04: The effect of crystalline environment on molecular interactions in crystals : A further (unknown) variable in crystal engineering	Enrique Espinosa University of Lorraine, France
9:40-10:05AM	A05: Continuous crystallization of pharmaceuticals	Richard Lakerveld The Hong Kong University of Science & Technology, Hong Kong
10:05-10:20AM	Session Break	
Session: Epitaxial thin films and nanostructures I Chair: Bernd Rauschenbach		
10:20 -10:45AM	A06: Stability and Electrical ZnIn ₂ O ₄ Thin Film with Cubic Spinel Structure as a Novel Transparent Conductive Oxide	Naoki Wakiya Shizuoka University, Japan
10:45-11:10AM	A07: Sub-monolayer InAs/GaAs depositions without and with Sb for fast, directly driven laser devices	Holger Eisele Technische Universität Berlin, Germany
11:10-11:35AM	A08: Real time observation of nanowire growth and selective growth of nanocrystals	Tomas Sikola Brno University of Technology, Czech Republic
11:35-12:00PM	A09: Novel Dilute Bismides for IR Optoelectronics	Shumin Wang Chalmers University of Technology, Sweden
12:00-12:25PM	A10: Magnetic domain wall manipulation in tailored (Ga,Mn)As nanostructures for spintronic applications	Tadeusz Wosinski Polish Academy of Sciences, Poland
12:30-13:30PM	Lunch Break	

Monday Dec. 14

Room B

Session: Epitaxial thin films and nanostructures II Chair: Tadeusz Wosinski

13:30-13:55PM	B01: Sheathed Nanowires Aligned by Crystallographic Periodicity	Hiroshi M. Yamamoto Institute for Molecular Science, Japan
13:55-14:20PM	B02: 3D Nanostructured Materials via Atomic Layer Deposition: Fabrication & Solar Energy Harvesting / Smart Window Applications	Alfred Tok Nanyang Technological University, Singapore
14:20-14:45PM	B03: SiGe Sputter Epitaxy and Its Application to SiGe 2D Devices	Yoshiyuki Suda Tokyo University of Agriculture and Technology, Japan
14:45-15:00PM	B04: Development of MBE Air-Hole Retained Growth Technique for Fabrication of Photonic-Crystal Lasers	Masaya Nishimoto Kyoto University, Japan
15:00-15:15PM	B05: Synthesis of High Performance Co(Soft)/SmCo5(Hard) Nanocomposite Magnets by Core/Shell Nanoparticles for Exchange-coupled Nanocomposite	Inho Kim Sogang University, Korea
15:15-15:25PM	Session Break	
Session: Epitaxial thin films and nanostructures III Chair: Yoshiyuki Suda		
15:25-15:50PM	B06: Epitaxial GaN films prepared by hyperthermal ion beam assisted molecular beam epitaxy - an electronmicroscopical study	Bernd Rauschenbach IOM and University Leipzig, Germany
15:50-16:15PM	B07: Concurring kinetics of phase transition and grain growth in nanostructured alloy	Feng Liu Northwestern Polytechnical University, China
16:15-16:40PM	B08: Epitaxial Growth of Lead-free Piezoelectric Thin films and Superlattices	Danyang Wang University of New South Wales, Australia
16:40-17:05PM	B09: The unique physical properties of nanostructured diamond	Changzhi Gu Institute of Physics, CAS, China
17:30PM	Dinner Social	

Monday Dec. 14

Room C

Session: 2D atomic layered materials I Chair: Toshio Ogino

13:30-13:55PM	C01: Latent heat induced rotation limited aggregation in 2D nanocrystalline ice	Bene Poelsema University of Twente, The Netherlands
13:55-14:20PM	C02: Tracking Atoms, Vacancies and Electrons via Aberration-corrected Microscopy and First-Principles Theory	Stephen Pennycook National University of Singapore, Singapore
14:20-14:45PM	C03: Growth and functionalization of epitaxial graphene on SiC	Wataru Norimatsu Nagoya University, Japan
14:45-15:10PM	C04: Germanene: the germanium analogue of graphene	Harold J. W. Zandvliet University of Twente, The Netherlands
15:10-15:25PM	Session Break	
Session: Radiation Detector Materials-From Crystal Growth to Device Applications I Chair: Jingxia Wang		
15:25-15:50PM	C05: New cerium doped elpasolite single crystal scintillators for radiation detection and medical imaging applications	HongJoo Kim Kyungpook National University, Korea
15:50-16:15PM	C06: Development of Novel Room Temperature Semiconductor Detector (RTSD) Materials and Devices	Sudhir Trivedi Brimrose Technology Corporation, USA
16:15-16:40PM	C07: Crack-free growth of large diameter Strontium Iodide scintillator crystals using innovative dehydration and matrix softening techniques	Amlan Datta Capesym, Inc., USA
16:40-17:05PM	C08: Features of radiation-induced processes in LiF crystals containing nanoscale impurity conglomerates	Liudmila Lisitsyna Tomsk State University of Architecture and Building, Russia
17:30PM	Dinner Social	

Monday Dec. 14

Room D

Session: Tunable materials Chair: Holger Eisele

13:30-13:55PM	D01: Gold(I) Compounds with Tunable Luminescent Properties	Andrea Deak Hungarian Academy of Sciences, Hungary
13:55-14:20PM	D02: Controlled nucleation and growth in glass and its impact on glass bioactivity	Jonathan Massera Tampere University of Technology, Finland
14:20-14:45PM	D03: Thin films from topological crystalline insulators	Marta Galicka Polish Academy of Sciences, Poland
14:45-15:10PM	D04: Glass-ferroic composite: the third class of ferroic materials	Yuanchao Ji Xi'an Jiaotong University, China
15:10-15:25PM	Session Break	

Session: General I Chair: Geun Woo Lee

15:25-15:50PM	D05: Importance of water in the control of inorganic crystal growth by organic molecules	Hiroki Nada National Institute of Advanced Industrial Science and Technology (AIST) Japan
15:50-16:15PM	D06: Synthesis of Graphene / $MxWO_3$ Composite with Excellent Electrical Properties	Shu Yin Tohoku University, Japan
16:15-16:40PM	D07: Convection diffusion models accompanied with gas-phase epitaxy of semiconducting layers	Pavel Boldyrevskii Nizhny Novgorod Lobachevsky State University, Russia
16:40-17:05PM	D08: Fluoride crystals as potential vacuum ultraviolet laser media	Nobuhiko Sarukura Osaka University, Japan
17:30PM	Dinner Social	

Tuesday Dec. 15		
Room B		
7:00-8:00AM	Breakfast	
Session: Epitaxial thin films and nanostructures IV Chair: Elisabeth Blanquet		
8:00-8:25AM	B10: Eliminating defects in three-dimensional micro- and nanocrystals on mismatched substrates	Hans Von Känel ETH Zürich, Switzerland
8:25-8:50AM	B11: Growth of atomically flat diamond films	Norio Tokuda Kanazawa University, Japan
8:50-9:15AM	B12: Hybrid Magnetic/Semiconductor Materials : Growth, Structure and Properties	Yongbing Xu Nanjing University, China; The University of York, UK
9:15-9:40AM	B13: Heteroepitaxial growth of layered pnictides and chalcogenides films	Hidenori Hiramatsu Tokyo Institute of Technology, Japan
9:40-10:05AM	B14: Epitaxial growth of gamma-phase Ga ₂ O ₃ semiconductor	Takayoshi Oshima Tokyo Institute of Technology, Japan
10:05-10:20AM	Session Break	
Session: General II Chair: Pallavi Kushwaha		
10:20 -10:45AM	B15: Lattice Model Analysis Combined with LEEM Observations	Noriko Akutsu Osaka Electro-Communication University, Japan
10:45-11:10AM	B16: Numerical Simulation of Development of Sea Ice Microstructure with Particle Method and Voronoi Dynamics	Yoshiki Kawano National Institute of Technology, Japan
11:10-11:35AM	B17: Structure-function correlations in metal oxides – Insights from density functional and many body theory	Eva Rauls Universität Paderborn, Germany
11:35-12:00PM	B18: Bipartite bosonic modes and spin memory effects in superconducting Sr ₄ V ₂ O ₆ Fe ₂ As ₂ investigated with variable temperature/field spin-polarized STM	Jhinhwan Lee KAIST, Korea
12:00-13:30PM	Lunch Break	
Session: General III Chair: Yoshiki Kawano		

13:30-13:55PM	B19: Real-Time Measurement of surface stress evolution during nano-structural formation on Silicon	Hidehito Asaoka Japan Atomic Energy Agency, Japan
13:55-14:20PM	B20: Valence band structure of monoclinic gallium oxide studied by polarized optical measurements	Takeyoshi Onuma Kogakuin University, Japan
14:20-14:45PM	B21: New trends in metallic Delafossite Materials	Pallavi Kushwaha Max-Planck Institute For Chemical Physics of Solids, Germany
14:45-15:10PM	B22: Scaling relation of domain competition on (2+1) dimensional ballistic deposition model with surface diffusion	Hiroyasu Katsuno Ritsumeikan University, Japan
15:10-15:55PM	Poster Session	
Session: General IV Chair: Takeshi Mitani		
15:55-16:20PM	B23: Thin film growth of BaSi2 photovoltaic material by rapid thermal evaporation	Kosuke O. Hara University of Yamanashi, Japan
16:20-16:35PM	B24: Morphologies of primary and eutectic silicon in hypereutectic Al-Si alloys under a low-voltage alternating current pulse	Limin Zhang Northwestern Polytechnical Univieristy, China
16:35-16:50PM	B25: High Magnetic Properties of Nano-sized Permanent Magnet Nd ₂ Fe ₁₄ B : Synthesis and Characterization	Jihun Jung Sogang University, Korea
16:50-17:05PM	B26: Bifunctional Transmission Film Composed of Phosphors and Gold Nanoparticles for Perovskite Solar Cell	Taeyoung Eom Sogang University, Korea
17:30PM	Dinner Social	

Tuesday Dec. 15		
Room C		
7:00-8:00AM	Breakfast	
Session: III-Nitrides for Lighting, Photovoltaics and Sensing Applications I		
Chair: Zlatko Sitar		
8:00-8:25AM	C09: Photoelectric energy conversion in GaN porous nanostructures formed by electrochemical process	Taketomo Sato Hokkaido University, Japan
8:25-8:50AM	C10: Solar Light Driven Selective Methanol Production via Artificial Photosynthesis Devices Fabrication	YoungSoo Kang Sogang University, Korea
8:50-9:15AM	C11: Dislocation Passivation by Positive Usage of Phase Separation During InGaN Growth by DERI Method	Yasushi Nanishi Ritsumeikan University, Japan
9:15-9:40AM	C12: Technical issues of GaInN growth with high indium composition for LEDs	Tohru Honda Kogakuin University, Japan
9:40-10:05AM	C13: Precise Growth Control for AlGaIn/GaN Superlattices by MBE and MOCVD for Developing GaN-Based THz Quantum Cascade Lasers	Wataru Terashima RIKEN Quantum Optodevice Laboratory, Japan
10:05-10:20AM	Session Break	
Session: 2D atomic layered materials II Chair: Bene Poelsema		
10:20 -10:45AM	C14: Nanopatterning of Graphene Films by Local Catalytic Etching Using Metal Nanoparticles	Toshio Ogino Yokohama National University, Japan
10:45-11:10AM	C15: Soft-mode instabilities and electronic correlations in strained 2D materials	Chris A. Marianetti Columbia University, USA
11:10-11:35AM	C16: Controlling the Space Distribution of Composition and Electronic Structure in Two dimensional Layered Semiconductor	Xidong Duan Hunan University, China
12:00-13:30PM	Lunch Break	
Session: Single crystals I Chair: Jarkko Leiro		
13:30-13:55PM	C17: Stability of micro and nano single crystal rods and wires	Harris Wong Louisiana State University, USA

13:55-14:20 PM	C18: Single-crystal film growth of organic semiconductors using inkjet printing	Hiromi Minemawari National Institute of Advanced Industrial Science and Technology (AIST), Japan
14:20-14:45PM	C19: Single crystal growth of Fe-Ga alloys by the Czochralski method for application to vibration energy harvesting	Shun Fujieda Tohoko University, Japan
14:45-15:10PM	C20: Single Crystal Growth for Functional Materials	Youguo Shi Institute of Physics, CAS China
15:10-15:55PM	Poster Session	
Session: Epitaxial thin films and nanostructures V Chair: Bernd Rauschenbach		
15:55-16:20PM	C21: In situ X-ray synchrotron and optical analysis of ZnO Growth by Atomic Layer Deposition	Elisabeth Blanquet University of Grenoble Alpes, France
16:20-16:45PM	C22: Pulsed laser deposition of epitaxial silicon carbide and aluminum nitride thin films on silicon substrates	Hideki Nakazawa Hirosaki University, Japan
16:45-17:10PM	C23: InGaAs and InP grown on silicon for high mobility CMOS	Jiaoqing Pan Institute of semiconductors, CAS, China
17:30PM	Dinner Social	

Tuesday Dec. 15		
Room D		
7:00-8:00AM	Breakfast	
Session: Crystal engineering II Chair: Kader Zaidat		
8:00-8:25AM	D09: Integrated Hybrid Semiconductors: Structural, Chemical, and Electrical Properties	Mark Goorsky University of California, Los Angeles, USA
8:25-8:50AM	D10: Influence on carrier recombination of Cu(In,Ga)Se ₂ solar cells induced by device processing	Jiro Nishinaga National Institute of Advanced Industrial Science and Technology (AIST), Japan
8:50-9:15AM	D11: H-Bond Stitched Nano-Porous Molecular Framework Materials	Jean-Pascal Sutter CNRS, Coordination Chemistry Lab (LCC), France
9:15-9:40AM	D12: Experimental and numerical aspects of the Kyropoulos Crystal Growth of Silicon for Photovoltaics	Guy Chichignoud SIMAP EPM CNRS, France
9:40-10:05AM	D13: Characterization of the dendrite structure during solidification: A study using synchrotron X-ray tomography and 3-D phase field modeling approaches	Zhipeng Guo Tsinghua University, China
10:05-10:20AM	Session Break	
Session: Single crystals II Chair: Harris Wong		
10:20-10:45AM	D14: Crystal Growth and piezoelectric properties of Ca ₃ Ta(Ga _{1-x} Al _x) ₃ Si ₂ O ₁₄ single crystals	Tetsuo Kudo Tohoku University, Japan
10:45-11:10AM	D15: Cleavage properties of muscovite mica and PbS single crystals	Jarkko Leiro University of Turku, Finland
11:10-11:35AM	D16: Comparisons between 5 at% Yb-doped LuPO ₄ and Yb-doped Lu _{0.5} Y _{0.5} PO ₄ crystals on absorption spectra	Bing Teng Qingdao University, China
12:00-13:30PM	Lunch Break	
Session: III-Nitrides for Lighting, Photovoltaics and Sensing Applications II Chair: YoungSoo Kang		
13:30-13:55PM	D17: Growth of Thick InGaN and GaN by Tri-Halide Vapor Phase Epitaxy with high rate	Hisashi Murakami Tokyo University of Agriculture & Technology, Japan

13:55-14:20PM	D18: Surface kinetics and surface morphology in MOCVD growth on III-nitride substrates	Zlatko Sitar North Carolina State University, USA
14:20 -14:45 PM	D19: Chemical vapor deposition of aluminium nitride from halide precursors for thin films and coatings	Michel Pons University of Grenoble Alpes, France
14:45-15:10PM	D20: High speed growth of InN by HVPE realized by controlled generation of InCl ₃	Rie Togashi Tokyo University of Agriculture and Technology, Japan
15:10-15:55PM	Poster Session	
Session: Crystal engineering III Chair: Mark Goorsky		
15:55-16:20PM	D21: Phase Transformations and Structure-Property Relationships in Ceramics	Cristian V. Ciobanu Colorado School of Mines, USA
16:20-16:45PM	D22: Phase Transformation of Calcium-based Minerals to Remove Fluoride from Aqueous Solutions	Il Won Kim Soongsil University, Korea
16:45-17:00PM	D23: Materials crystallization at mesoscale	Dongfeng Xue Changchun Institute of Applied Chemistry, CAS, China
17:30PM	Dinner Social	

Wednesday Dec. 16		
Room B		
7:00-8:00AM	Breakfast	
Session: Radiation Detector Materials - From Crystal Growth to Device Applications II		
Chair: HongJoo Kim		
8:00-8:25AM	B27: Facile fabrication of porphyrin Janus particles from water droplet template at oil-aqueous interface	Jingxia Wang Technical Institute of Physics and Chemistry, China
8:25-8:50AM	B28: GaSb alternative substrates for MBE growth of next generation HgCdTe infrared detectors	Wen Lei University of Western Australia, Australia
Session: III-Nitrides for Lighting, Photovoltaics and Sensing Applications III		
Chair: Yasushi Nanishi		
8:50-9:15AM	B29: Preparation of III-Nitride Devices for Large Area Light Emitting Devices and Solar Cells	Hiroshi Fujioka The University of Tokyo, Japan
9:15-9:40AM	B30: Recent Advances in Basic Ammonothermal Growth of Gallium Nitride	Siddha Pimputkar University of California, USA
9:40-10:05AM	B31: InGaN pyramidal quantum dot as a source of single photons	Houssaine Machhadani Linköping University, Sweden
10:05-10:20AM	Session Break	
Session: Crystal engineering IV Chair: Zhipeng Guo		
10:20-10:45AM	B32: Layer crystal growth with fractal analysis technique: from theory to engineering application	Xiaobin Jiang Dalian University of Technology, China
10:45-11:10AM	B33: Engineering Functional Materials by Halogen Bonding	Giancarlo Terraneo Politecnico di Milano, Italy
11:10-11:35AM	B34: Crystal growth control in chalcogenide and its application to multilevel storage in phase-change memory	You Yin Gunma University, Japan
12:00-13:30 PM	Lunch Break	
Session: Epitaxial thin films and nanostructures VI Chair: Sylke Blumstengel		
13:30-13:55PM	B35: Monolithic integrated Ge light emitters fabricated by epitaxial lateral overgrowth	Katsuya Oda Hitachi Ltd., Research & Development Group, Japan

13:55-14:20PM	B36: Atomically Engineered Metal-Insulator Transition at the TiO ₂ /LaAlO ₃ Heterointerface	Makoto Minohara High Energy Accelerator Research Organization (KEK), Japan
14:20 -14:45 PM	B37: Thermodynamics and kinetics of nanocluster formation on semiconductor surfaces	Andreas Fissel Leibniz University Hannover, Germany
14:45-15:10PM	B38: Epitaxial growth of metastable oxide thin films under atmosphere	Kentaro Kaneko Kyoto University, Japan
15:10-15:25PM	Session Break	
Session: Epitaxial thin films and nanostructures VII Chair: Hans Von Känel		
15:25-15:45PM	B39: Growth and Characterization of Full Flux-closure Quadrants in PbTiO ₃ thin films	Yinlian Zhu Institute of Metal Research, CAS, China
15:45-16:10PM	B40: Synthesis of Polar and Non-Polar Epitaxial GaN Thin Films by Ion-Beam Nitridation of Ga Droplets	Jürgen W. Gerlach Leibniz Institute of Surface Modification (IOM), Germany
16:10-16:35PM	B41: Epitaxial growth of hybrid inorganic/organic semiconductor structures	Sylke Blumstengel Humboldt-Universität zu Berlin, Germany
16:35-17:00PM	B42: Epitaxially stabilized oxide film composed of twisted triangular-lattice layers	Masaki Uchida The University of Tokyo, Japan
17:00-17:25PM	B43: Growth temperature dependence of crystalline state of low-temperature-grown InGaAs on InP substrate	Yoriko Tominaga Hiroshima University, Japan
17:30PM	Dinner Social	

Wednesday Dec. 16 Room C		
7:00-8:00AM	Breakfast	
Session: General V Chair: Jean-Noel Aqua		
8:00-8:25AM	C24: Supercooled liquids, glasses and growth of dendrites under out of equilibrium conditions	Francesco Aliotta Istituto per I Processi Chimici-Fisici, CNR Italy
8:25-8:50AM	C25: Electric Field Assisted Growth of Organic Conductive wire and Self-aligned Organic Nanotransistor	Masatoshi Sakai Chiba University, Japan
8:50-9:15AM	C26: Calcium minerals crystal growth for dental material applications	Yuki Sugiura Kyushu University, Japan
9:15-9:40AM	C27: Morphology effect on the nano-hematite and its magnetic property	Yen-Hua Chen National Cheng Kung University, Taiwan
9:40-10:05AM	C28: Dynamics of Multi-functional Materials with Inelastic Neutron Scatterings	Dehong Yu Australian Nuclear Science and Technology Organisation, Australia
10:05-10:20AM	Session Break	
Session: General VI Chair: Alexander Gelfgat		
10:20-10:45AM	C29: Structural diversity of multi-component self-assembled systems	Irene Ling University of Malaya, Malaysia
10:45-11:10AM	C30: Magnetocaloric effect in multifunctional perovskites	Suja Elizabeth Indian Institute of Science, India
11:10-11:35AM	C31: Strain-engineered SiGe nanomembranes on Porous Silicon stressor	Jean-Noel Aqua Universit éParis 6 – INSP, France
11:35-12:00PM	C32: Silicon Nanostructures for Nanoelectronics and Photovoltaics	Noushine Shahidzadeh University of Amsterdam, The Netherlands
12:00-13:30 PM	Lunch Break	
Session: Crystal engineering V Chair: Guy Chichignoud		

13:55-14:20PM	C33: Morphology Control of Metal Oxide Crystals for Multifunctional Cosmetic Application	Tsugio Sato Tohoku University, Japan
14:20-14:45PM	C34: Crystal engineering of cocrystals: air-stable cyclohexasulfur as cocrystal	Kunihisa Sugimoto Japan Synchrotron Radiation Research Institute (JASRI), Japan
14:45 -15:10PM	C35: Drug beneficiation via cyclodextrin inclusion	Mino R. Caira University of Cape Town, South Africa
15:10-15:25PM	Session Break	
Session: Crystal engineering VI Chair: Kader Zaidat		
15:25 -15:50PM	C36: The discrete crystal growth: multi-scale phenomena, mechanism and influence on segregation	Xiaoping Ma Institute of Metal Research, CAS, China
15:50-16:15PM	C37: In Situ Study of the Crystal Formation Process of Molecular Materials	Yang Liu Shandong University, China
16:15-16:40PM	C38: Wetting and joining of structural materials by growth of metal borates nano/micro whiskers	Jian Cao Harbin Institute of Technology, China
17:30PM	Dinner Social	

Wednesday Dec. 16		
Room D		
7:00-8:00AM	Breakfast	
Session: Epitaxial thin films and nanostructures VIII Chair: Kosuke Matsuzaki		
8:00-8:25AM	D24: Growth of strained Si/SiGe on Si(110) substrates for realization of high-mobility devices	Keisuke Arimoto University of Yamanashi, Japan
8:25-8:50AM	D25: Construction of well-defined 3D transition metal oxides nanostructures and their novel properties	Azusa N. Hattori Osaka University, Japan
8:50-9:15AM	D26: A-site driven ferroelectricity in strained La ₂ NiMnO ₆ thin films	Ryota Takahashi University of Tokyo, Japan
9:15-9:40AM	D27: Synthesis of Heteroatom-Containing Nanocarbon Materials by Solution Plasma Process in Organic Solution	Takahiro Ishizaki Shibaura Institute of Technology, Japan
9:40-10:05AM	D28: Modified InAs/GaAs quantum dots for enhanced solar cell efficiency	Jose Mar ^á Ulloa Universidad Polit ^é cnica de Madrid, Spain
10:05-10:20AM	Session Break	
Session: Epitaxial thin films and nanostructures IX Chair: Masaki Uchida		
10:20-10:45AM	D29: Low Temperature Deposition of Epitaxial (K,Na)NbO ₃ Films using Hydrothermal Method	Takahisa Shiraishi Tohoku University, Japan
10:45-11:10AM	D30: Epitaxial Growth of InAs-based Quantum Structures on GaAs	Itaru Kamiya Toyota Technological Institute, Japan
11:10-11:35AM	D31: Epitaxial growth of bipolar conducting Cu ₃ N (100) thin films	Kosuke Matsuzaki Tokyo Institute of Technology, Japan
11:35-12:00PM	D32: A-axis Growth of nano structured VO ₂ Thin films by Pulsed Laser Deposition on substrate glass	Balla Diop Ngom Universit Cheikh Anta Diop de Dakar (UCAD), Senegal
12:00-13:30PM	Lunch Break	
Session: General VII Chair: Masaharu Oshima		
13:55-14:20PM	D33: Non-intrusive instability measurements in a model of Czochralski melt flow	Alexander Gelfgat Tel Aviv University, Israel

14:20 -14:45 PM	D34: Thermal conductive graphene quantum dots for the electromagnetic interference	Hyonkwang Choi Inje University, Korea
14:45 -15:10 PM	D35: Multiple pathway of nucleation from levitated solution droplets	Geun Woo Lee Korea Research Institute of Standards and Science, Korea
15:10-15:25PM	Session Break	
Session: General VIII Chair: Francesco Aliotta		
15:25-15:50PM	D36: Solution growth of 4H-SiC crystals with Si and Si based alloy solvents	Takeshi Mitani National Institute of Advanced Industrial Science and Technology, Japan
15:50-16:15PM	D37: Operando spectronanoscropy for graphene FET and ultrathin organic film FET	Masaharu Oshima The University of Tokyo, Japan
16:15-16:40PM	D38: Metastability Limit for the Nucleation of NaCl Crystals in Confinement	Daniel Bonn University of Amsterdam, The Netherlands
17:30PM	Dinner Social	

Tuesday Dec. 15

15:10-15:55PM

Poster Session

P01	Electrical and optical properties of ZnO films prepared by solution film forming method	Saki Fukui Tohoku University Japan
P02	Inkjet Printing Patterned Photonic Crystal Domes for Wide Viewing-angle by the Sliding Three Phase Contact Line	Minxuan Kuang Institute of Chemistry, CAS China
P03	Morphological Controlled Synthesis of ZnO for the application to sunscreen cosmetic	Mizuki Yoshida Tohoku University Japan
P04	Synthesis and NIR-Shielding Ability of Nb-doped TiO ₂ by Solvothermal Approach	Makoto Hsmanaka Tohoku University Japan
P05	Single crystal growth of SiC using high temperature chemical vapor deposition from methyltrichlorosilane	Seongmin Jeong Korea Institute of Ceramic Engineering and Technology (KICET) Korea
P06	Crystal Growth and Superconductivity of half-Heusler Compounds ErPdBi and HoPdBi	Yingkai Huang University of Amsterdam The Netherlands
P07	Solvothermal synthesis of ternary ZnSSe nanorods with tunable band gap and its photoluminescence enhancement	Lin-Jer Chen National Cheng Kung University Taiwan